

**IN THE SPECIFICATION:**

**Please insert the following on Page 1, (below the title):**

**--CROSS-REFERENCE TO RELATED APPLICATION**

This application is a divisional of U.S. application Serial No. 09/683,625, filed January 28, 2002.--

**LISTING OF THE CLAIMS:**

Claims 1-10 (Cancelled)

11. (Original) A Fin structure comprising:

a structure having at least one vertically oriented semiconductor body present thereon,  
wherein said at least one vertically oriented semiconductor body has vertical surfaces;

a doped region present in said at least one vertically oriented semiconductor body that  
extends inward from said vertical surfaces; and

contacts present on outer portions of said at least one vertically oriented semiconductor  
body, wherein said doping region and said contacts are of the same dopant type thereby  
providing a resistor in said at least one vertically oriented semiconductor body.